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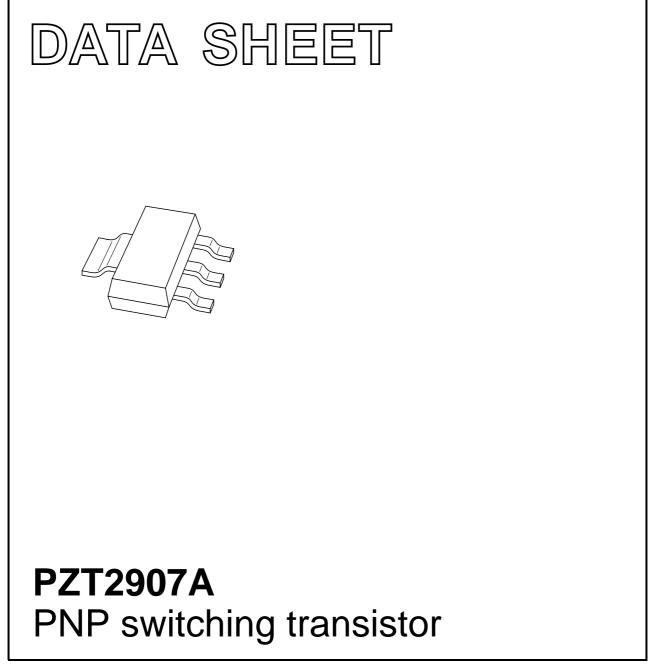
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

## DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1997 Jun 02 1999 Apr 14



## PZT2907A

#### FEATURES

- High current (max. 600 mA)
- Low voltage (max. 60 V).

#### APPLICATIONS

• Switching and linear amplification.

#### DESCRIPTION

PNP switching transistor in a SOT223 plastic package. NPN complement: PZT2222A.

#### PINNING

PIN	DESCRIPTION	
1	base	
2, 4	collector	
3	emitter	

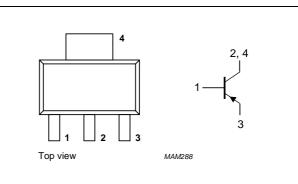


Fig.1 Simplified outline (SOT223) and symbol.

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	-	-60	V
V <sub>CEO</sub>	collector-emitter voltage	open base	—	-60	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	-5	V
I <sub>C</sub>	collector current (DC)		_	-600	mA
I <sub>CM</sub>	peak collector current		—	-800	mA
I <sub>BM</sub>	peak base current		-	-200	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	—	1.15	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

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#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	106	K/W	
R <sub>th j-s</sub>	thermal resistance from junction to soldering point		25	K/W	

#### Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>. For other mounting conditions, see *"Thermal considerations for SOT223 in the General Part of associated Handbook"*.

#### CHARACTERISTICS

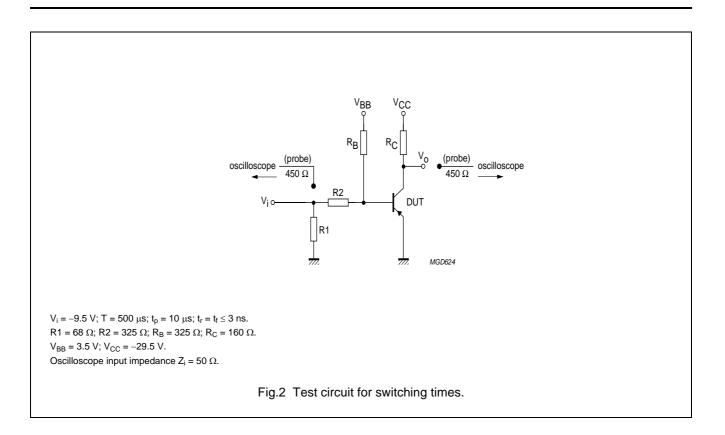
 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current	$I_E = 0; V_{CB} = -50 V$	-	-10	nA
		$I_E = 0; V_{CB} = -50 \text{ V}; T_{amb} = 150 \text{ °C}$	-	-10	μA
I <sub>EBO</sub>	emitter cut-off current	$I_{C} = 0; V_{EB} = -5 V$	-	-50	nA
h <sub>FE</sub>	DC current gain	$I_{C} = -0.1 \text{ mA}; V_{CE} = -10 \text{ V}$	75	_	
		$I_{C} = -1 \text{ mA}; V_{CE} = -10 \text{ V}$	100	_	
		$I_{C} = -10 \text{ mA}; V_{CE} = -10 \text{ V}$	100	_	
		$I_{C} = -150 \text{ mA}; V_{CE} = -10 \text{ V}; \text{ note } 1$	100	300	
		$I_{C} = -500 \text{ mA}; V_{CE} = -10 \text{ V}; \text{ note } 1$	50	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{\rm C} = -150 \text{ mA}; I_{\rm B} = -15 \text{ mA}; \text{ note } 1$	_	-400	mV
		$I_{\rm C} = -500 \text{ mA}; I_{\rm B} = -50 \text{ mA}; \text{ note } 1$	-	-1.6	V
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{\rm C} = -150 \text{ mA}; I_{\rm B} = -15 \text{ mA}; \text{ note } 1$	-	-1.3	V
		$I_{\rm C} = -500 \text{ mA}; I_{\rm B} = -50 \text{ mA}; \text{ note } 1$	-	-2.6	V
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0; V_{CB} = -10 V; f = 1 MHz$	-	8	pF
C <sub>e</sub>	emitter capacitance	$I_{C} = i_{c} = 0; V_{EB} = -2 V; f = 1 MHz$	_	30	pF
f <sub>T</sub>	transition frequency	$I_{\rm C} = -50 \text{ mA}; V_{\rm CE} = -20 \text{ V};$	200	_	MHz
		f = 100 MHz; note 1			
Switching t	imes (between 10% and 90% levels)	; (see Fig.2)	•	-	
t <sub>on</sub>	turn-on time	$I_{Con} = -150 \text{ mA}; I_{Bon} = -15 \text{ mA};$	_	40	ns
t <sub>d</sub>	delay time	I <sub>Boff</sub> = 15 mA	-	12	ns
t <sub>r</sub>	rise time		-	30	ns
t <sub>off</sub>	turn-off time	]	_	365	ns
t <sub>s</sub>	storage time	]	-	300	ns
t <sub>f</sub>	fall time		_	65	ns

#### Note

1. Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 

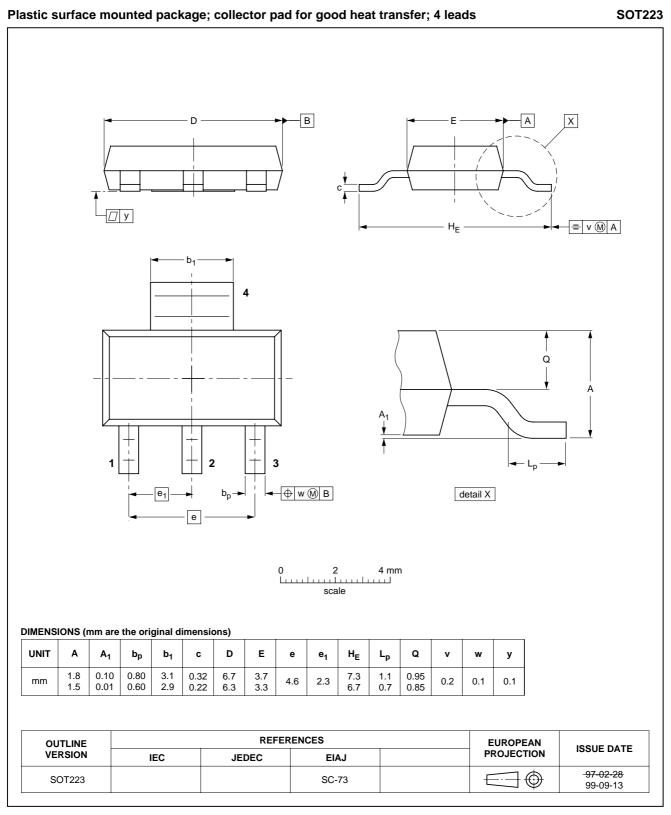
## PZT2907A



PZT2907A

## PNP switching transistor

#### PACKAGE OUTLINE



PZT2907A

#### DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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## **NXP Semiconductors**

#### **Customer notification**

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#### **Contact information**

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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